www.omseni.com

OM SENI

MBRB1045T4G, MBRD1045T4G, SBRB1045T4G, SBRD81045T4G Switch-mode Schottky Power Rectifier

Surface Mount Power Package

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal−to−silicon power diode. State−of−the−art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

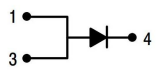
Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Short Heat Sink Tab Manufactured − Not Sheared!
- SBRB and SBRD8 Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

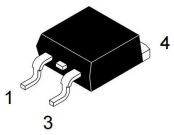
Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V−0
- Weight: 1.7 grams for D^2PAK (approximately)
  0.4 grams for DPAK (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
  - Machine Model = C (> 400 V)
  - Human Body Model = 3B (> 8000 V)

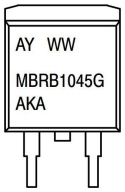
SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 45 VOLTS



MARKING DIAGRAM

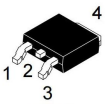


D^2PAK CASE 418B

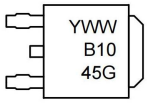


A	= Assembly Location
Y	= Year
WW	= Work Week
MBRB1045	= Device Code
G	= Pb−Free Package
AKA	= Diode Polarity

MARKING DIAGRAM



DPAK CASE 369C



Y	= Year
WW	= Work Week
B1045	= Device Code
G	= Pb−Free Package

OM SENI

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R) T_C = 135°C	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) T_C = 135°C	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150 (MBRB/SBRB) 70 (MBRD/SBRD)	A
Operating Junction and Storage Temperature Range (Note 1)	T_J, T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, (MBRB1045G) Junction−to−Case (Note 2) Junction−to−Ambient (Note 2) (MBRD1045G) Junction−to−Case (Note 2) Junction−to−Ambient (Note 2)	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JC}$ $R_{\theta JA}$	 1.0 50 2.43 68	°C/W

2. When mounted using minimum recommended pad size on FR−4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) (I_F = 10 Amps, T_J = 125°C) (I_F = 20 Amps, T_J = 125°C) (I_F = 20 Amps, T_J = 25°C)	V_F	 0.57 0.72 0.84	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	I_R	 15 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

ORDERING INFORMATION

Device	Package	Shipping†
MBRB1045T4G	D^2PAK (Pb−Free)	800 Units / Tape & Reel
SBRB1045T4G		800 Units / Tape & Reel
MBRD1045T4G	DPAK (Pb−Free)	2,500 Units / Tape & Reel
SBRD81045T4G		2,500 Units / Tape & Reel
SSBRD81045T4G		2,500 Units / Tape & Reel

OM SENI

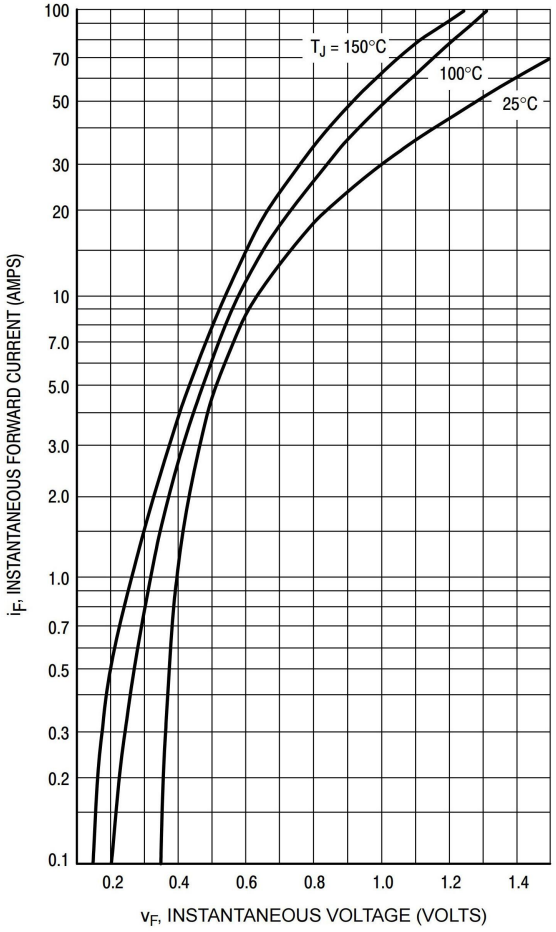


Figure 1. Maximum Forward Voltage

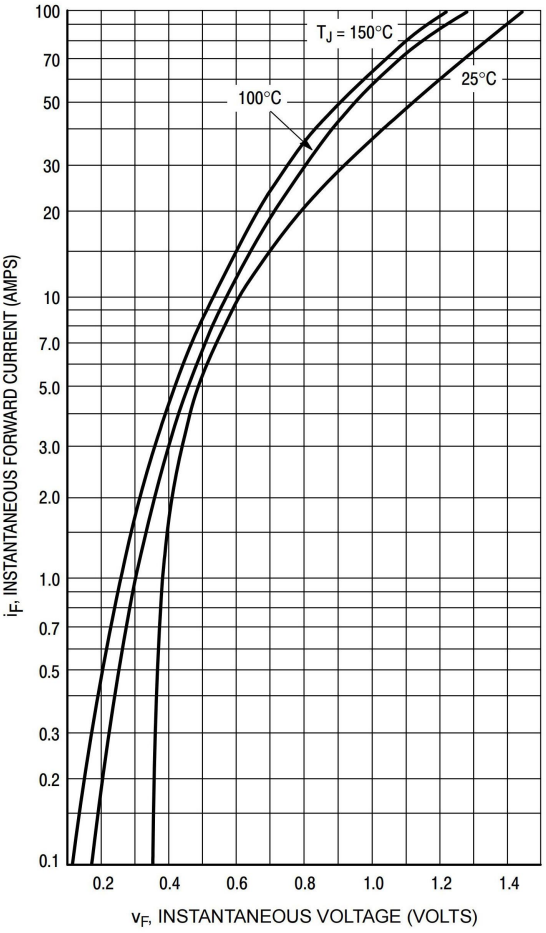


Figure 2. Typical Forward Voltage

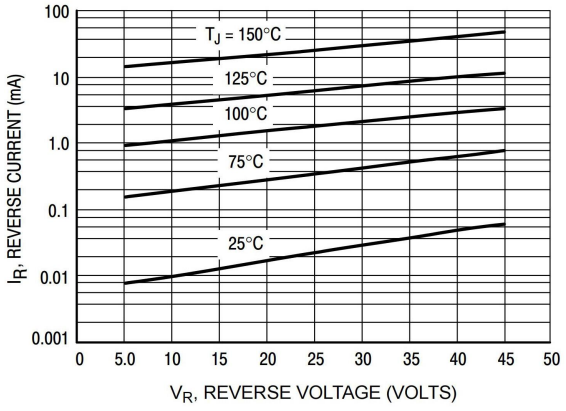


Figure 3. Maximum Reverse Current

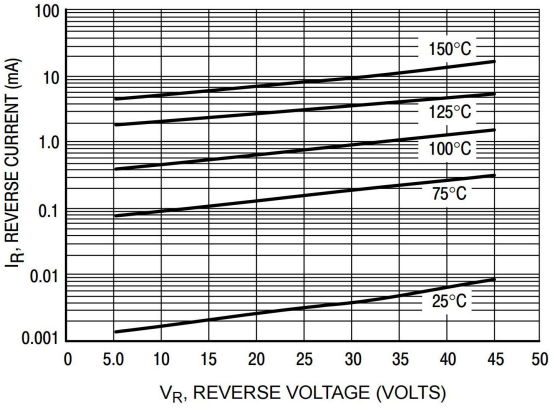


Figure 4. Typical Reverse Current

OM SENI

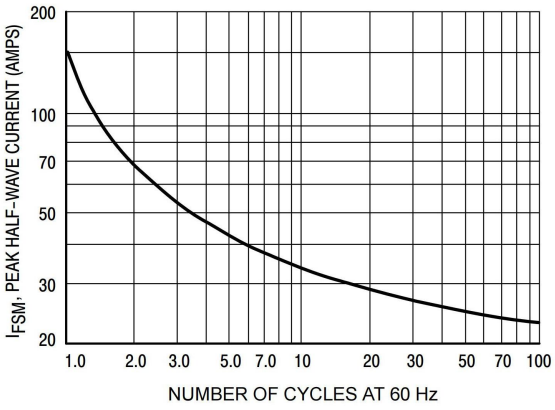


Figure 8. Maximum Surge Capability

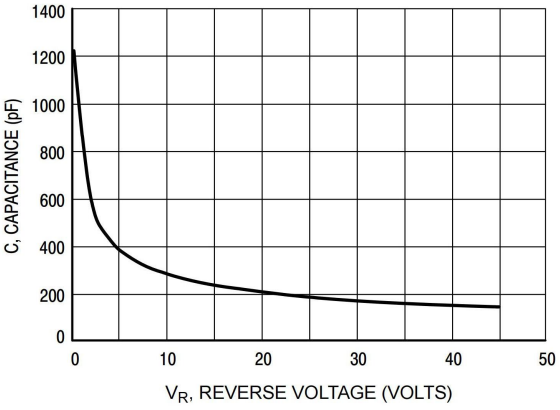


Figure 5. Typical Capacitance

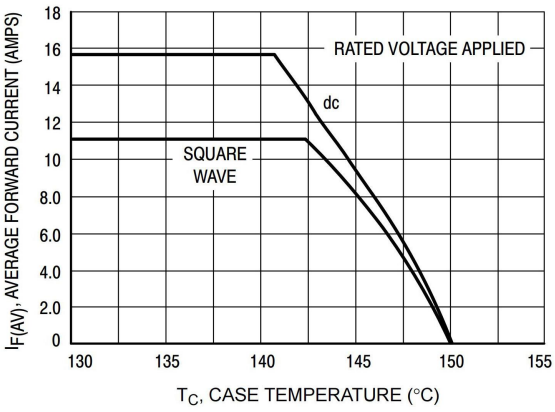


Figure 6. Current Derating, Case,
$R_{\theta JC}$ = 1.0 °C/W

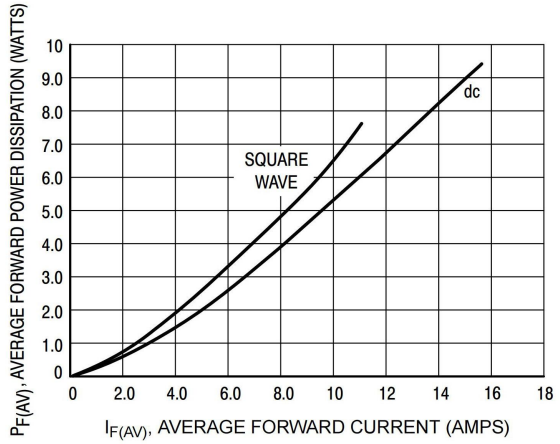
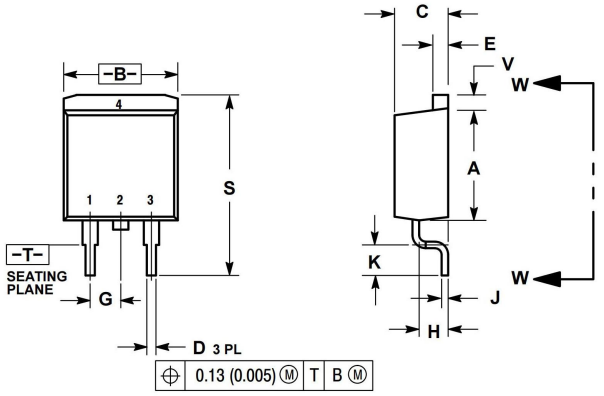


Figure 7. Forward Power Dissipation

OM SENI

PACKAGE DIMENSIONS

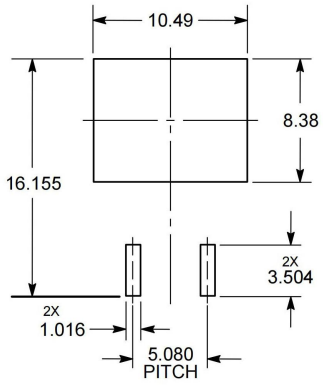
D²PAK 3
CASE 418B−04
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B−01 THRU 418B−03 OBSOLETE, NEW STANDARD 418B−04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

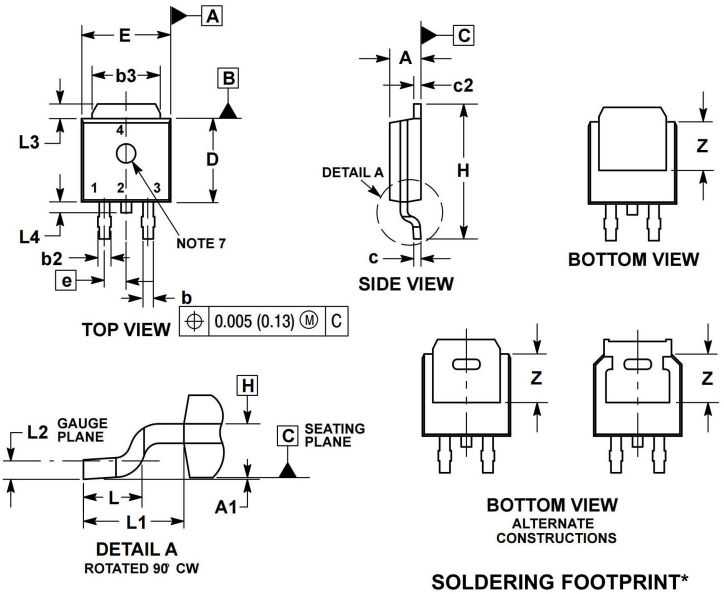
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

OM SENI

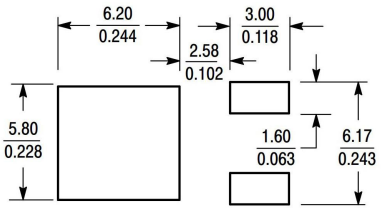
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)